

# 2SA564, 2SA564A

## Silicon PNP Epitaxial Planar Type

For general amplification

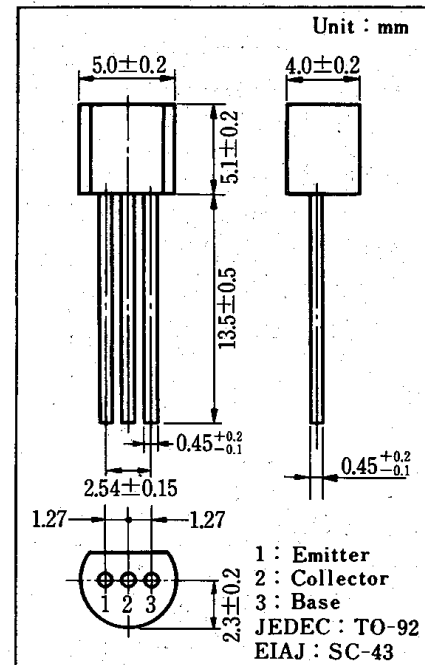
### ■ Features

- Large DC current gain  $h_{FE}$

### ■ Absolute Maximum Ratings ( $T_a=25^\circ\text{C}$ )

Item	Symbol	Value	Unit
Collector-Base Voltage	2SA564	-25	V
	2SA564A	-45	
Collector-Emitter Voltage	2SA564	-25	V
	2SA564A	-45	
Emitter-Base Voltage	$V_{EBO}$	-7	V
Peak Collector Voltage	$I_{CP}$	-200	mA
Collector Current	$I_C$	-100	mA
Collector Power Dissipation	$P_C$	400	mW
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 ~ +150	$^\circ\text{C}$

### ■ Package Dimensions



### ■ Electrical Characteristics ( $T_a=25^\circ\text{C}$ )

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = -20\text{ V}, I_E = 0$			-1	$\mu\text{A}$
	$I_{CEO}$	$V_{CE} = -20\text{ V}, I_B = 0$			-10	
Collector-Base Voltage	$V_{CBO}$	$I_C = -10\mu\text{A}, I_E = 0$	-25			V
			-45			
Collector-Emitter Voltage	$V_{CEO}$	$I_C = -2\text{ mA}, I_B = 0$	-25			V
			-45			
Emitter-Base Voltage	$V_{EBO}$	$I_E = -10\mu\text{A}, I_C = 0$	-7			V
DC Current Gain	$h_{FE}^*$	$V_{CE} = -5\text{ V}, I_C = -2\text{ mA}$	130		520	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -50\text{ mA}, I_B = -2.5\text{ mA}$			-1	V
Transition Frequency	$f_T$	$V_{CB} = -10\text{ V}, I_E = 2\text{ mA}, f = 200\text{ MHz}$		150		MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$		3.5		pF

\*  $h_{FE}$  Ranking

Rank	Q	R	S
$h_{FE}$	130 ~ 260	180 ~ 360	260 ~ 520

